

Features

- Frequency: 90GHz~95GHz
- Linear Gain: 12dB
- Psat: 27dBm
- +15V@0.3A
- Chip Size: 3.42mm×1.40mm×0.05mm

Electrical Specification (TA=+25°C, Vd=+15V, Vg=-2.2V)

Parameter	Min.	Typ.	Max.	Unit
Frequency	90-95			GHz
Psat	27			dBm
Power Gain	8			dB
VSWRin/out			3:1	-
Operating Current		300		mA

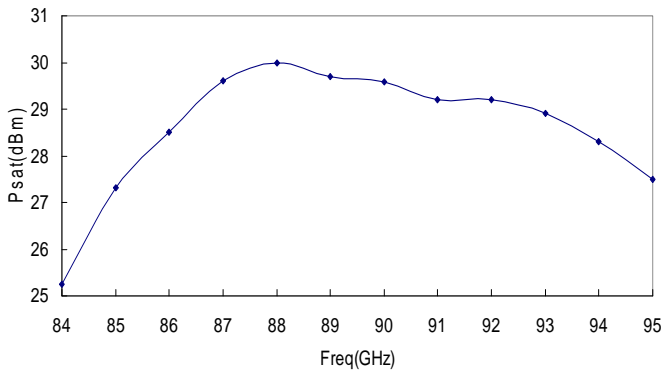
Note: 1) RF Test Condition: Vd=+15V, Vg=-2.2V, Pin=19dBm, CW

Limited Rating Values

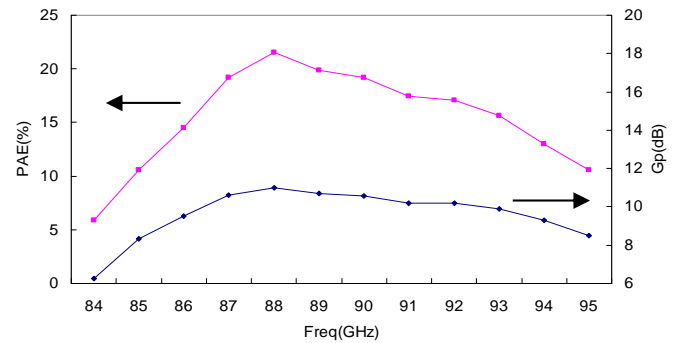
Max. Vds	+18V
Min. Vgs	-5V
Max. Input Power	+21dBm
Operating Temperature	-55°C ~ +125°C
Storage Temperature	-65°C ~ +150°C

Typical Testing Curves

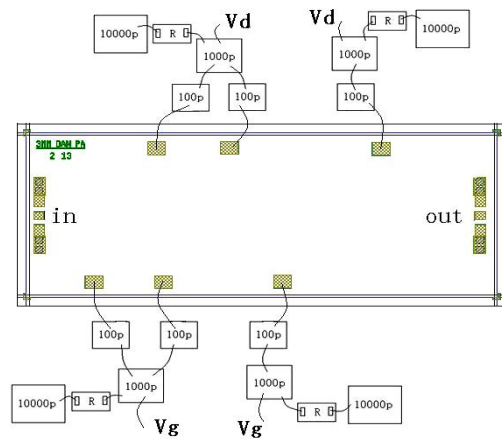
Psat vs. Frequency



P.A.E./Power Gain vs. Frequency

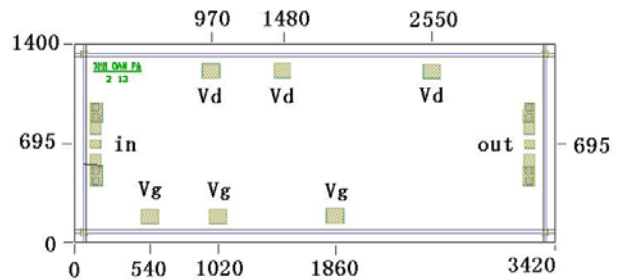


Assembly Diagram



Note: R=10Ω

Dimensions and Outline



Attention

- 1) Gold wires (diameter: 25μm~30μm) are suggested to be used. The temperature of bonding platform should not exceed 250°C.
- 2) Antistatic protection should be taken.